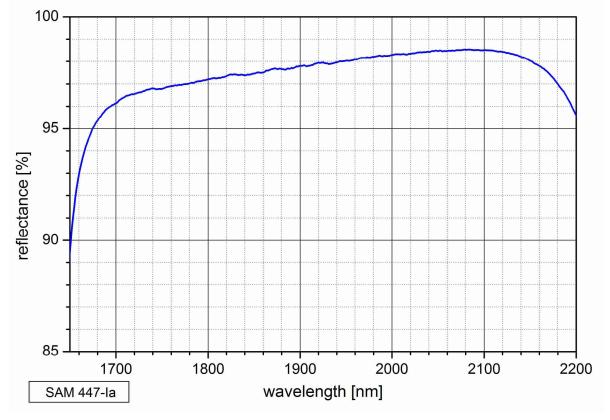
1



## SAM™ Data Sheet SAM-2000-2-10ps-x, λ = 2000 nm

Laser wavelength	$\lambda = 2000 \text{ nm}$
High reflection band	λ = 1700 2150 nm
Absorbance	$A_0 = 2 \%$
Modulation depth	∆R = 1.2 %
Non-saturable loss	A <sub>ns</sub> = 0.8 %
Saturation fluence	$\Phi_{sat}$ = 70 µJ/cm <sup>2</sup>
Relaxation time constant	τ ~ 10 ps
Damage threshold	$\Phi$ = 4 mJ/cm <sup>2</sup>
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	625 μm
Design	laser beam goes through the AR coated GaAs substrate
Mounting option <b>x</b> denotes the <b>x</b> = 0 <b>x</b> = 12.7 g <b>x</b> = 25.4 g	unmounted

## Low intensity spectral reflectance





## Reverse design of the SAM-2000-2-10ps-x

